**Product data sheet** 

## 1. General description

High voltage, high speed, planar passivated NPN power switching transistor in a SOT54 (TO-92) plastic package.

### 2. Features and benefits

- Fast switching
- High typical DC current gain
- High voltage capability of 700 V
- · Very low switching and conduction losses

## 3. Applications

- Compact fluorescent lamps (CFL)
- Low power electronic lighting ballasts
- · Off-line self-oscillating power supplies (SOPS) for battery charging

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>C</sub>	collector current	DC		-	-	1.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>		-	-	2.1	W
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-	700	V
Static characte	Static characteristics						
h <sub>FE</sub>	DC current gain	$I_C$ = 0.5 A; $V_{CE}$ = 2 V; $T_{lead}$ = 25 °C		8	17	25	
		$I_C$ = 1 A; $V_{CE}$ = 2 V; $T_{lead}$ = 25 °C		5	9	15	

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## **5. Pinning information**

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	С	collector		В
3	Е	emitter		E sym123
			TO-92 (SOT54)	sy20

## 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PHE13003C	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54		

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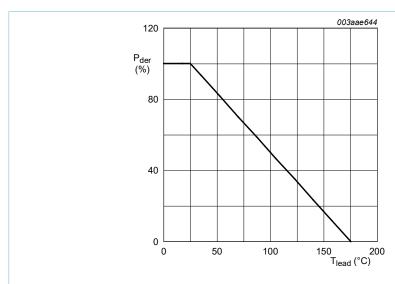
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# 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	700	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	700	V
$V_{CEO}$	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
$V_{EBO}$	emitter-base voltage	I <sub>C</sub> = 0 A; I(Emitter) = 10 mA	-	9	V
I <sub>C</sub>	collector current	DC	-	1.5	Α
I <sub>CM</sub>	peak collector current		-	3	Α
I <sub>B</sub>	base current	DC	-	0.75	Α
I <sub>BM</sub>	peak base current		-	1.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>lead</sub> ≤ 25 °C; <u>Fig. 1</u>	-	2.1	W
T <sub>stg</sub>	storage temperature		-65	150	°C
T <sub>j</sub>	junction temperature		-	150	°C



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig. 1. Normalized total power dissipation as a function of lead temperature

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	<u>Fig. 2</u>	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air; printed circuit board mounted; lead length = 4 mm	-	150	-	K/W

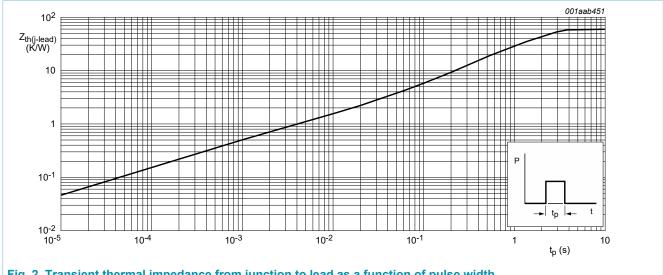


Fig. 2. Transient thermal impedance from junction to lead as a function of pulse width

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## 9. Characteristics

#### **Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 125 °C	-	-	5	mA
	current (base shorted)	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 700 V; T <sub>j</sub> = 25 °C	-	-	1	mA
I <sub>CEO</sub>	collector-emitter cut-off current (base open)	$V_{CE} = 400 \text{ V}; I_{B} = 0 \text{ A}; T_{lead} = 25 \text{ °C}$	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V}; I_{C} = 0 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	1	mA
$V_{CEOsus}$	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 1 \text{ mA}; L_C = 25 \text{ mH};$ $T_{lead} = 25 \text{ °C}; \underline{Fig. 3}; \underline{Fig. 4}$	400	-	-	V
V <sub>CEsat</sub>	collector-emitter	$I_C = 0.5 \text{ A}; I_B = 0.1 \text{ A}; T_{lead} = 25 ^{\circ}\text{C}$	-	-	0.5	V
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 0.25 A; T <sub>lead</sub> = 25 °C	-	-	1	V
		I <sub>C</sub> = 1.5 A; I <sub>B</sub> = 0.5 A; T <sub>lead</sub> = 25 °C	-	-	1.5	V
$V_{BEsat}$	base-emitter saturation	I <sub>C</sub> = 0.5 A; I <sub>B</sub> = 0.1 A; T <sub>lead</sub> = 25 °C	-	-	1	V
	voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 0.25 A; T <sub>lead</sub> = 25 °C	-	-	1.2	V
h <sub>FE</sub>	DC current gain	$I_C = 0.5 \text{ A}; V_{CE} = 2 \text{ V}; T_{lead} = 25 ^{\circ}\text{C}$	8	17	25	
		I <sub>C</sub> = 1 A; V <sub>CE</sub> = 2 V; T <sub>lead</sub> = 25 °C	5	9	15	
Dynamic cl	haracteristics		'			
t <sub>on</sub>	turn-on time	I <sub>C</sub> = 1 A; I <sub>Bon</sub> = 0.2 A; I <sub>Boff</sub> = -0.2 A;	-	-	1	μs
t <sub>s</sub>	storage time	$R_L = 75 \Omega$ ; $T_{lead} = 25 ^{\circ}C$ ; resistive load; Fig. 5; Fig. 6	-	-	4	μs
		$I_C$ = 1 A; $I_{Bon}$ = 0.2 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; <u>Fig. 7</u> ; <u>Fig. 8</u>	-	0.8	-	μs
t <sub>f</sub>	fall time	$I_C$ = 1 A; $I_{Bon}$ = 0.2 A; $I_{Boff}$ = -0.2 A; $R_L$ = 75 $\Omega$ ; $T_{lead}$ = 25 °C; resistive load; Fig. 5; Fig. 6	-	-	0.7	μs
		$I_C$ = 0.5 A; $I_{Bon}$ = 0.1 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_{lead}$ = 25 °C; inductive load; Fig. 7; Fig. 8	-	0.1	-	μs

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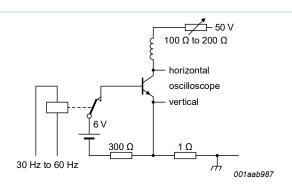


Fig. 3. Test circuit for collector-emitter sustaining voltage

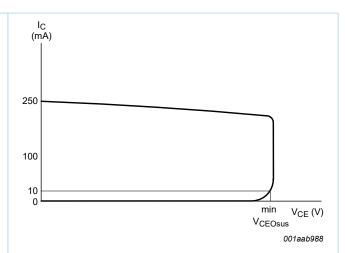
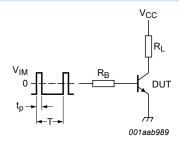


Fig. 4. Oscilloscope display for collector-emitter sustaining voltage test waveform



 $V_{IM}$  = -6 to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu$ s;  $\delta$  =  $\frac{t_p}{T}$  = 0.01  $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig. 5. Test circuit for resistive load switching

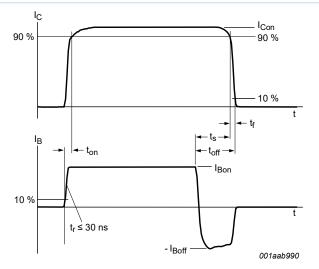
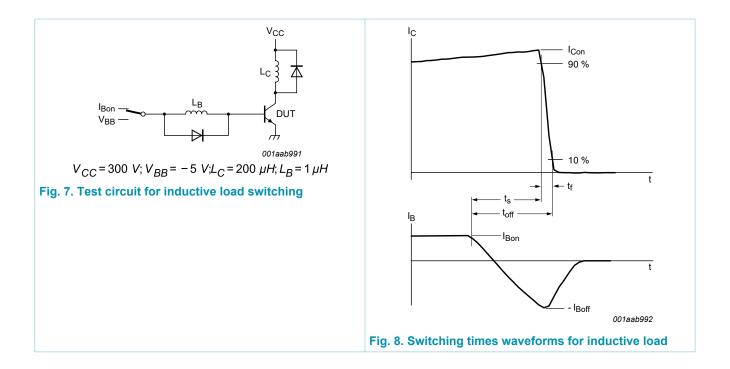
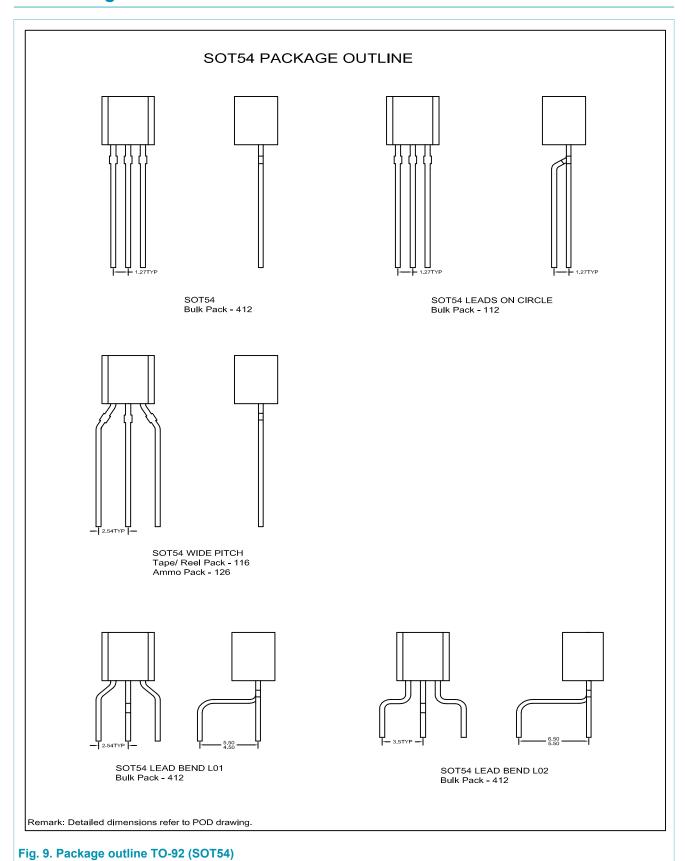


Fig. 6. Switching times waveforms for resistive load

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## 10. Package outline



PHE13003C

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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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